



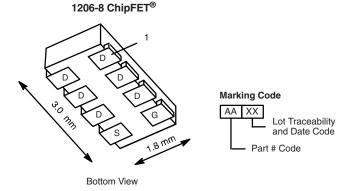
N-Channel 30 V (D-S) MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)		
30	0.035 at V _{GS} = 10 V	± 6.7		
	0.055 at V _{GS} = 4.5 V	± 5.3		

FEATURES

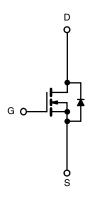
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFETs
- · Compliant to RoHS Directive 2002/95/EC





Ordering Information: Si5402DC-T1-E3 (Lead (Pb)-free)

Si5402DC-T1-GE3 (Lead (Pb)-free and Halogen-free)



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted						
Parameter		Symbol	5 s	Steady State	Unit	
Drain-Source Voltage		V _{DS}	30		V	
Gate-Source Voltage		V _{GS}	± 20			
Continuous Drain Current /T 150 °C\2	T _A = 25 °C	- I _D	± 6.7	± 4.9		
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 85 °C		± 4.8	± 3.5		
Pulsed Drain Current		I _{DM}	± 20		Α	
Continuous Source Current (Diode Conduction) ^a		I _S	2.1	1.1	İ	
Mariana Barra Birainating	T _A = 25 °C	- P _D	2.5	1.3	W	
Maximum Power Dissipation ^a	T _A = 85 °C		1.3	0.7		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C	
Soldering Recommendations (Peak Temperature) ^{b, c}			260			

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Marrian Institut to Archiomta	t ≤ 5 s	- R _{thJA}	40	50	°C/W
Maximum Junction-to-Ambient ^a	Steady State		80	95	
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	15	20	

Notes:

- a. Surface mounted on 1" x 1" FR4 board..
- b. See Reliability Manual for profile. The ChipFET is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- c. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.

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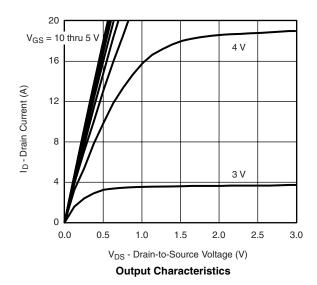
SPECIFICATIONS T _J = 25 °C, unless otherwise noted							
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1.0			V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
Zara Cata Valtaria Direia Communit	I _{DSS}	V _{DS} = 24 V, V _{GS} = 0 V			1	μΑ	
Zero Gate Voltage Drain Current		V _{DS} = 24 V, V _{GS} = 0 V, T _J = 85 °C			5		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	20			Α	
5	В	V _{GS} = 10 V, I _D = 4.9 A	0.030		0.035		
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 3.9 \text{ A}$		0.045	0.055	Ω	
Forward Transconductance ^a	9 _{fs}	$V_{DS} = 10 \text{ V}, I_D = 4.9 \text{ A}$		15		S	
Diode Forward Voltage ^a	V_{SD}	I _S = 1.1 A, V _{GS} = 0 V		0.8	1.2	V	
Dynamic ^b				•			
Total Gate Charge	Q_g			13	20		
Gate-Source Charge	Q_{gs}	$V_{DS} = 15 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 4.9 \text{ A}$		1.3		nC	
Gate-Drain Charge	Q_{gd}			3.1			
Turn-On Delay Time	t _{d(on)}			10	15		
Rise Time	t _r	V_{DD} = 15 V, R_L = 15 Ω		10	15	ns	
Turn-Off Delay Time	t _{d(off)}	$I_D\cong$ 1 A, V_{GEN} = 10 V, R_g = 6 Ω		25	40		
Fall Time	t _f			10	15		
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 1.1 A, dI/dt = 100 A/μs		30	60		

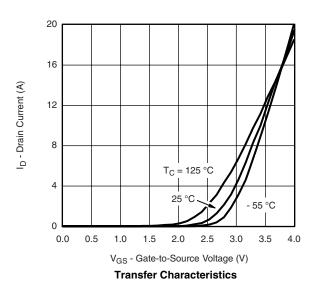
Notes:

- a. Pulse test; pulse width \leq 300 $\mu s,$ duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

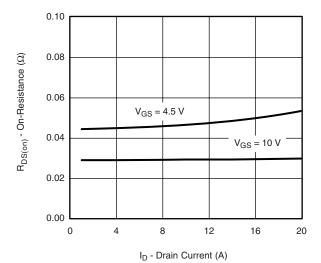




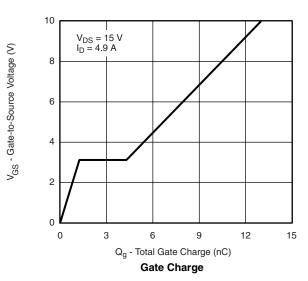


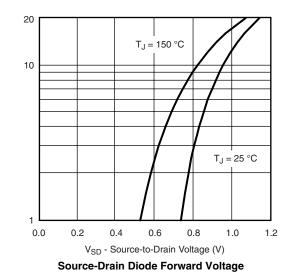


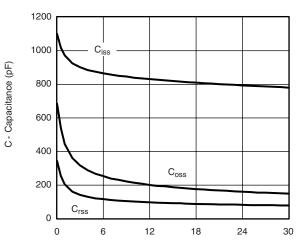
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On-Resistance vs. Drain Current

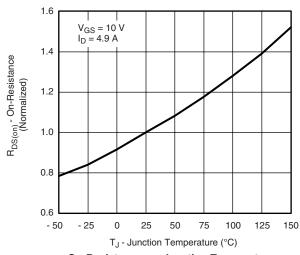




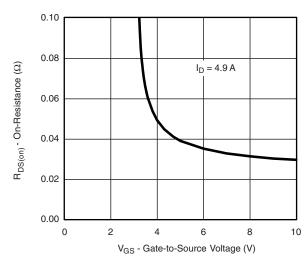


V_{DS} - Drain-to-Source Voltage (V)





On-Resistance vs. Junction Temperature



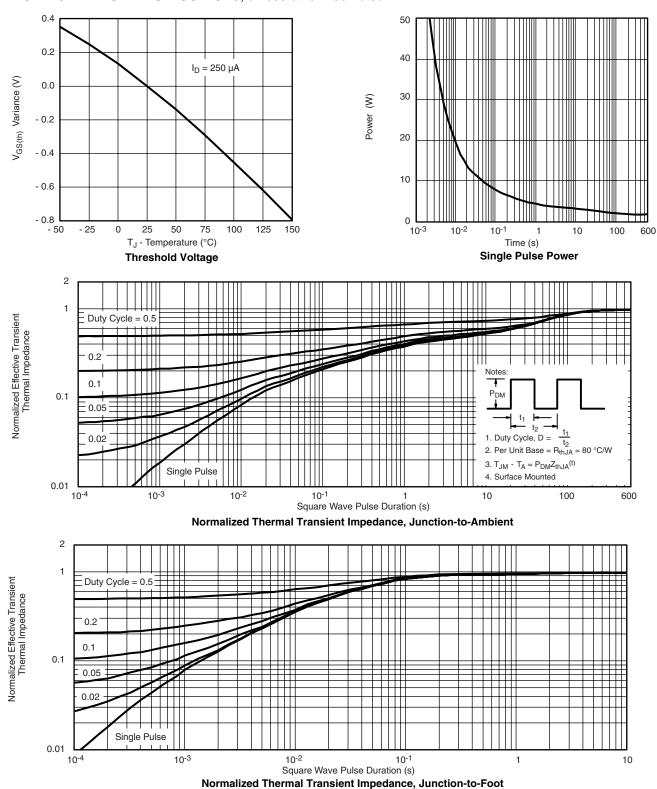
On-Resistance vs. Gate-to-Source Voltage

Is - Source Current (A)

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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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